

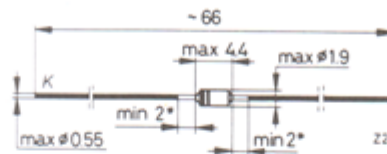
N 125

Silicon Epitaxial Planar Diode

for general purposes

Dimensions in mm

Band: cathode



* not tinned

Case: DO-35

Mass: approx. 0.15 g

Absolute maximum ratings

Reverse voltage	V_R	50	V
Forward current	I_F	150	mA
Junction temperature	T_j	150	°C
Storage temperature	T_s	-55 ... +150	°C
Total power dissipation	P_{tot}^1	300	mW

Thermal resistance

junction to ambient	R_{thja}	= 410	K/W
---------------------	------------	-------	-----

Static characteristics

$T_{amb} = 25^\circ\text{C}$

Forward voltage

$I_F = 100\text{ mA}$

V_F	≤ 1	V
-------	----------	---

Reverse current

$V_R = 35\text{ V}$

I_R	≤ 100	nA
-------	------------	----

Dynamic characteristics

$T_{amb} = 25^\circ\text{C}$

Diode capacitance

$V_R = 0\text{ V}, f = 1\text{ MHz}$

C_D	≤ 2	pF
-------	----------	----

¹ $T_L \leq 45^\circ\text{C}, L = 4\text{ mm}$